

LISTING OF THE CLAIMS

1. (Previously Presented) A process of growing a thin film of Al₂O₃ on a substrate in a reaction chamber by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising:

exposing the substrate in the reaction chamber to gaseous trimethyl aluminum (TMA);
stopping provision of the gaseous TMA;
removing gaseous TMA from the reaction chamber;
exposing the substrate in the reaction chamber to atomic oxygen; and
removing atomic oxygen from the reaction chamber,
wherein in each cycle more than one monolayer of Al₂O₃ is formed.

2. (Original) The process of claim 1, wherein in each cycle a layer of Al₂O₃ 3 Å thick is formed.

3. (Previously Presented) The process of Claim 1, wherein the atomic oxygen is generated remotely in a radical generator.

4. (Original) The process of Claim 1, wherein the process is carried out at room temperature.

5. - 17. (Cancelled)

18. (Previously Presented) A process of growing a thin film of Al₂O₃ on a substrate in a reaction chamber by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising:

exposing the substrate in the reaction chamber to gaseous trimethyl aluminum (TMA);
stopping provision of the gaseous TMA;
removing gaseous TMA from the reaction chamber; and
exposing the substrate in the reaction chamber to atomic oxygen.

19. (Previously Presented) The process of Claim 18, wherein the atomic oxygen is generated remotely in a radical generator.

20. (Previously Presented) The process of Claim 18, wherein the process is carried out at room temperature.